

JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO.,LTD

TO-92 Plastic-Encapsulate Transistors

\$8550 TRANSISTOR (PNP)

FEATURE

Power dissipation

P_{CM} : 0.625 W (Tamb=25℃)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

V_{(BR)CBO}: -40 V

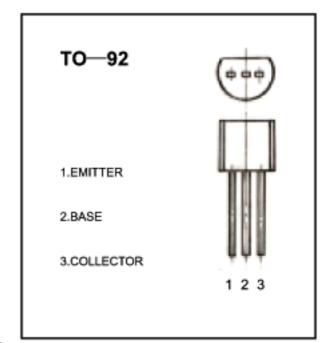
Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25 °C

unless otherwise specified)

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Parameter	Symbol	conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CB}	Ic= -100 μ A , I _E =0	-40			V
Collector-emitter breakdown voltage	V(BR) _{CE} o	Ic= -0.1 mA , I _B =0	-25			V
Emitter-base breakdown voltage	V(BR) _{EB}	I _E = -100 μ A , I _C =0	-5			V
Collector cut-off current	I _{CBO}	V_{CB} = -40 V , I_E =0			-0.1	μ А
Collector cut-off current	I _{CEO}	V _{CE} = -20 V , I _B =0			-0.2	μА
Emitter cut-off current	I _{EBO}	V _{EB} = - 3 V, I _C =0			-0.1	μА
DC current gain	H _{FE (1)}	V_{CE} = -1 V, I_{C} = -50mA	85		300	
DC current gam	H _{FE (2)}	V_{CE} = -1 V, I_{C} = -500mA	50			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =-500mA, I _B =-50 mA			-0.6	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =-500mA, I _B =-50 mA			-1.2	V
Base-emitter voltage	V _{BE}	I _E = -100mA			-1.4	V
Transition frequency	f⊤	V_{CE} =- 6 V, I_{C} =-20mA f =30MHz	150			MHz

Test

CLASSIFICATION OF H_{FE(1)}

Rank	В	С	D
Range	85-160	120-200	160-300